

Atty. Docket No. OPP031054US
Serial No: 10/734,818

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Amendments to the Specification

Please replace paragraph [0014] beginning at page 4, line 4 with the following replacement paragraph:

[0001] Next, as shown in Fig. 2b, the nitride layer 12 is etched using the photoresist pattern 13 as a mask. The photoresist pattern 13 is not removed, but remains after etching the nitride layer 12. ~~Subsequently~~Subsequently, the interlayer insulating layer 11 is etched using the photoresist pattern 13 as a mask as shown in Fig. 2c.

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